

DOCKET NO.: 219625US99DIV

#2 Pre Amndt. A
7-1-02
Ratula

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: : EXAMINER

JAMAL RAMDANI

SERIAL NO.: NEW DIVISIONAL APPL. :

FILED: HEREWITH : GROUP ART UNIT

FOR: SEMICONDUCTOR STRUCTURE, SEMICONDUCTOR DEVICE,
COMMUNICATING DEVICE, INTEGRATED CIRCUIT, AND PROCESS
FOR FABRICATING THE SAME

PRELIMINARY AMENDMENT

Sir:

Prior to examination on the merits, please enter the following Amendment.

IN THE CLAIMS

Please cancel Claims 1-143.

Please add new Claims 144-237.

--144. A semiconductor structure comprising:

a plurality of material layers including:

a monocrystalline silicon substrate;

a monocrystalline perovskite oxide material overlying at least a portion
of the monocrystalline silicon substrate;

an amorphous oxide material located between the monocrystalline
perovskite oxide material and the monocrystalline silicon substrate;

a monocrystalline compound semiconductor material overlying at least
a portion of the monocrystalline perovskite oxide material; and

205430 0543004

A'